Preferred Device

General Purpose Transistors

PNP Silicon

Features

WWW.DZSC.CON • Pb-Free Packages are Available*



Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	40	Vdc
Emitter – Base Voltage	V _{EBO}	5.0	Vdc
Collector Current – Continuous	Ic	200	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Power Dissipation @ T _A = 60°C	P _D	250	mW
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

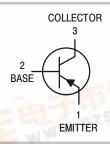
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates Data in addition to JEDEC Requirements.



ON Semiconductor®

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MARKING DIAGRAM



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.



ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

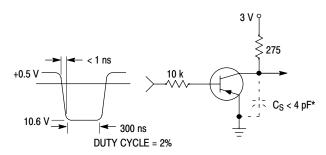
Characteristic			Symbol	Min	Max	Unit
OFF CHARACTERIST	rics			•	•	•
Collector - Emitter Brea	akdown Voltage (No	ote 2) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	40	_	Vdc
Collector - Base Break	down Voltage	$(I_C = 10 \mu Adc, I_E = 0)$	V _{(BR)CBO}	40	_	Vdc
Emitter – Base Breakdo	own Voltage	$(I_E = 10 \mu Adc, I_C = 0)$	V _{(BR)EBO}	5.0	_	Vdc
Base Cutoff Current		$(V_{CE} = 30 \text{ Vdc}, V_{EB} = 3.0 \text{ Vdc})$	I _{BL}	_	50	nAdc
Collector Cutoff Currer	Collector Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)		I _{CEX}	_	50	nAdc
ON CHARACTERISTIC	CS (Note 2)					
DC Current Gain		$ \begin{array}{l} (I_{C}=0.1 \text{ mAdc, V}_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=1.0 \text{ mAdc, V}_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=10 \text{ mAdc, V}_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=50 \text{ mAdc, V}_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=100 \text{ mAdc, V}_{CE}=1.0 \text{ Vdc}) \end{array} $	h _{FE}	60 80 100 60 30	- 300 - -	_
Collector - Emitter Satu	uration Voltage	$(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$ $(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	V _{CE(sat)}	- -	0.25 0.4	Vdc
Base – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$)			V _{BE(sat)}	0.65 -	0.85 0.95	Vdc
SMALL-SIGNAL CHA	ARACTERISTICS					
Current-Gain - Bandy	width Product	$(I_C = 10 \text{ mAdc}, V_{CE} = 20 \text{ Vdc}, f = 100 \text{ MHz})$	f _T	250	-	MHz
Output Capacitance		$(V_{CB} = 5.0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{obo}	_	4.5	pF
Input Capacitance		$(V_{EB} = 0.5 \text{ Vdc}, I_{C} = 0, f = 1.0 \text{ MHz})$	C _{ibo}	_	10	pF
Input Impedance (I _C		$(I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$	h _{ie}	2.0	12	kΩ
Voltage Feedback Ratio (I _C		$(I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$	h _{re}	0.1	10	X 10 ⁻⁴
Small–Signal Current Gain (I _C = 1.0 mAc		$(I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$	h _{fe}	100	400	_
Output Admittance ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)		h _{oe}	3.0	60	μmhos	
Noise Figure (I _C = 100 μ Adc, V _{CE} = 5.0 Vdc, R _S = 1.0 k Ω , f = 1.0 kHz)		NF	_	4.0	dB	
SWITCHING CHARAC	CTERISTICS					
Delay Time $(V_{CC} = 3.0 \text{ Vdc}, V_{BE} = 0.5 \text{ Vdc},$		t _d	_	35	ns	
Rise Time	I _C = 10 mAdc, I _{B1} = 1.0 mAdc)		t _r	_	35	ns
Storage Time	$(V_{CC} = 3.0 \text{ Vdc}, I_C = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc})$		t _s	-	225	ns
Fall Time	$(V_{CC} = 3.0 \text{ Vdc}, I_C = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc})$		t _f	_	75	ns

^{2.} Pulse Test: Pulse Width $\leq 300 \,\mu s$; Duty Cycle $\leq 2\%$.

ORDERING INFORMATION

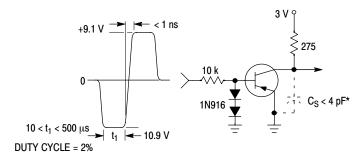
Device	Package	Shipping [†]
2N3906	TO-92	5000 Units / Bulk
2N3906G	TO-92 (Pb-Free)	5000 Units / Bulk
2N3906RL1	TO-92	5000 Units / Bulk
2N3906RL1G	TO-92 (Pb-Free)	5000 Units / Bulk
2N3906RLRA	TO-92	2000 / Tape & Reel
2N3906RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3906RLRM	TO-92	2000 / Ammo Pack
2N3906RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3906RLRP	TO-92	2000 / Tape & Reel
2N3906RLRPG	TO-92 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



^{*} Total shunt capacitance of test jig and connectors

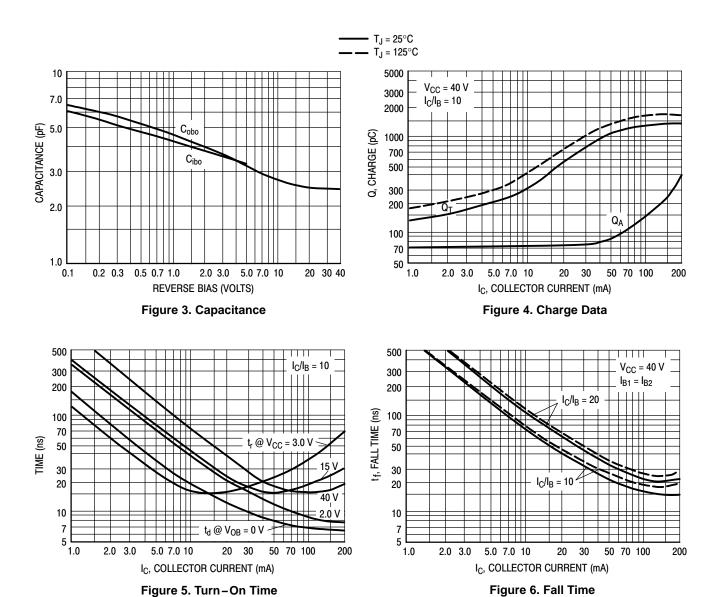
Figure 1. Delay and Rise Time Equivalent Test Circuit



^{*} Total shunt capacitance of test jig and connectors

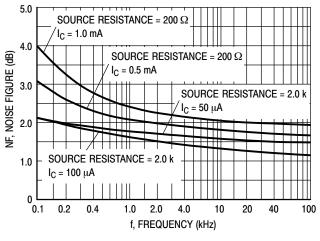
Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS



TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS **NOISE FIGURE VARIATIONS**

 $(V_{CE} = -5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$



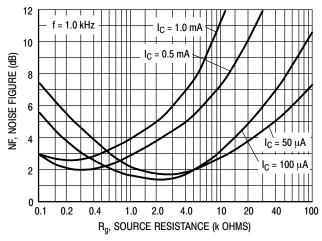
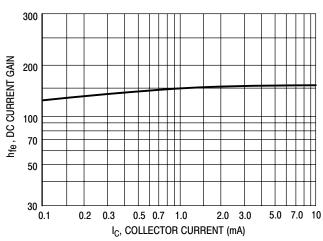


Figure 7.

Figure 8.

h PARAMETERS

 $(V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz}, T_A = 25^{\circ}\text{C})$



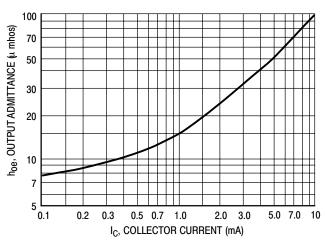
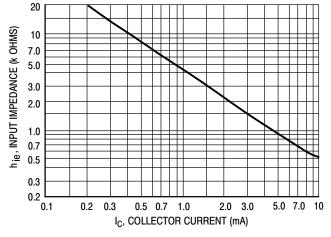


Figure 9. Current Gain

Figure 10. Output Admittance



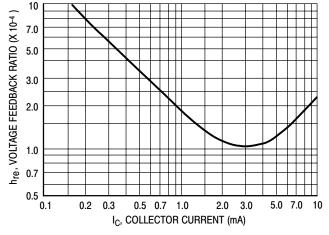


Figure 11. Input Impedance

Figure 12. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

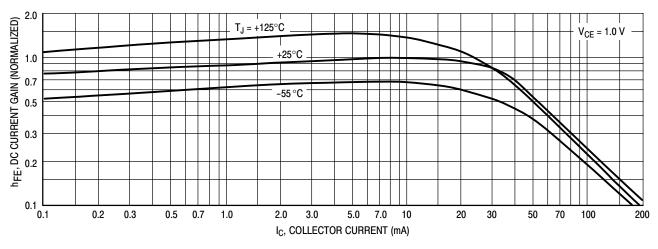


Figure 13. DC Current Gain

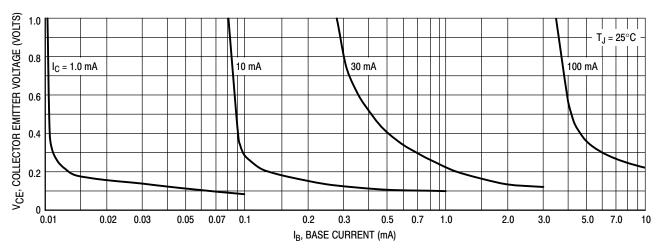


Figure 14. Collector Saturation Region

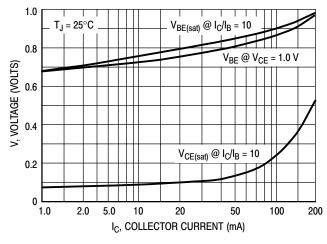


Figure 15. "ON" Voltages

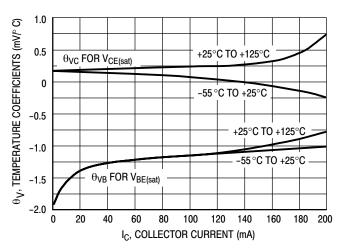
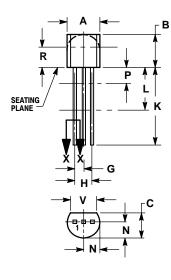


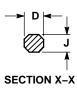
Figure 16. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**

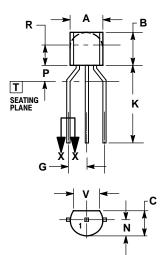


STRAIGHT LEAD **BULK PACK**



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R
- IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

_				
	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P	-	0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 CONTOUR OF PACKAGE BEYOND
 DIMENSION R IS UNCONTROLLED.

- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
٧	3.43		

STYLE 1:

PIN 1. EMITTER

2. BASE

COLLECTOR

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